

version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.

Cancel claims 1 and 11-15.

Sub C
2. (Amended) The method of claim 10 wherein the co-evaporating and depositing are conducted in a chamber, and wherein there is no O₂ flowed into the chamber during the co-evaporation and deposition.

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3. (Amended) The method of claim 10 wherein the co-evaporating comprises thermal evaporation of the aluminum oxide from single crystal sapphire.

4. (Amended) The method of claim 10 wherein the co-evaporating comprises thermal evaporation of the silicon monoxide.

5. (Amended) The method of claim 10 wherein the co-evaporating comprises ion beam evaporation of the aluminum oxide.

6. (Amended) The method of claim 10 wherein the co-evaporating comprises electron gun evaporation of the aluminum oxide.

7. (Amended) The method of claim 10 wherein the co-evaporating comprises:

thermal evaporation of the silicon monoxide; and

one or both of electron gun evaporation and ion beam evaporation of the aluminum oxide.

Sub C1
8. (Amended) The method of claim 10 wherein the substrate comprises silicon.

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9. (Amended) The method of claim 10 wherein the substrate comprises monocrystalline silicon.

10. (Amended) A method of forming an assembly comprising silicon-doped aluminum oxide, comprising:

co-evaporating aluminum oxide and silicon monoxide;

depositing at least some of the evaporated aluminum oxide and silicon monoxide on a semiconductive material substrate to form the silicon-doped aluminum oxide on the substrate; and

forming a conductive material on the deposited silicon-doped aluminum oxide, the conductive material being separated from the semiconductive material of the substrate by the silicon-doped aluminum oxide.